



#11/B  
Amend B w/ LCE  
Micronas.5903  
09/780,796  
J. Robinson  
9/30/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**APPLICANT:** Martin Czech et al. **GROUP:** 2811  
**SERIAL NO:** 09/780,976 ✓ **EXAMINER:** Steven Loke  
**FILED:** February 9, 2001  
**FOR:** LATERAL THYRISTOR STRUCTURE FOR PROTECTION  
AGAINST ELECTROSTATIC DISCHARGE

Honorable Commissioner of Patents  
and Trademarks  
Washington, D.C. 20231

Sir:

**SECOND AMENDMENT**

This amendment is in response to the Official Action dated March 11, 2003.

Please amend the application as follows:

IN THE SPECIFICATION:

Amend the paragraph starting on page 5, line 20 as follows:

31 Briefly, according to the present invention a lateral thyristor structure for protection against electrostatic discharge includes a semiconductor substrate of a first conduction type, with a surface and a well region of a second conduction type that is opposite to the first one and is introduced into the surface of the semiconductor substrate. A first strongly doped region of a second conduction type is introduced into the surface of the semiconductor substrate, and is electrically connected to a first terminal. A second strongly doped region of a first conduction type is introduced into the well region and is electrically connected to a second terminal. A third strongly doped region of another, second conduction type is introduced into the well region, and